

Green Products

SB6200 SCHOTTKY RECTIFIER

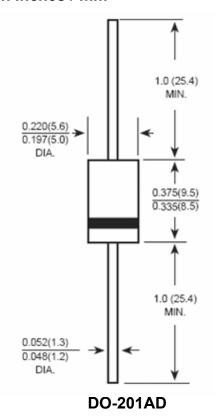
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

Features:

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In Inches / mm



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Marking Diagram:



Where XXXXX is YYWWL

SB = Device Type

6 = Forward Current (6A) 200 = Reverse Voltage (200V)

SSG = SSG YY = Year WW = Week

L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SB6200	DO-201AD	1250 pcs / tape
	(Pb-Free)	1230 pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Max. Average Forward	I _{F(AV)}	50% duty cycle @T _C =105°C, rectangular wave form	6.0	А
Max. Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	128	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 6 A, Pulse, T _J = 25 °C	0.90	V
Max. Reverse Current	I _{R1}	@V _R = rated VR	1.0	mA
	I _{R2}	$T_J = 25 ^{\circ}\text{C}$ @V _R = rated VR $T_J = 125 ^{\circ}\text{C}$	7.0	mA
Max. Junction Capacitance (per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	150	pF
Max. Voltage Rate of Change	dv/dt	-	10,000	V/us

^{*} Pulse Width < 300µs, Duty Cycle <2%

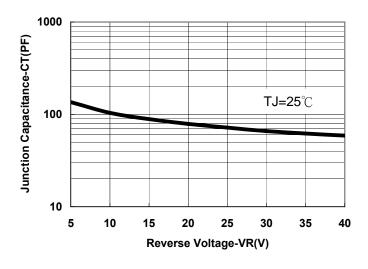
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature Range	TJ	-	-55 to +150	°C
Storage Temperature Range	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	3.5	°C/W
Approximate Weight	wt	-	1.02	g
Case Style	DO-201AD			

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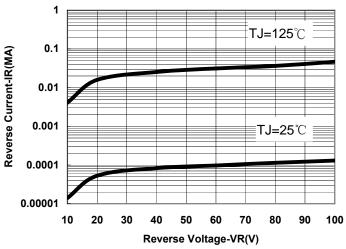


Fig.1-Typical Junction Capacitance Vs.Reverse Voltage

Fig.2-Typical Values Of Reverse Current Vs.Reverse Voltage

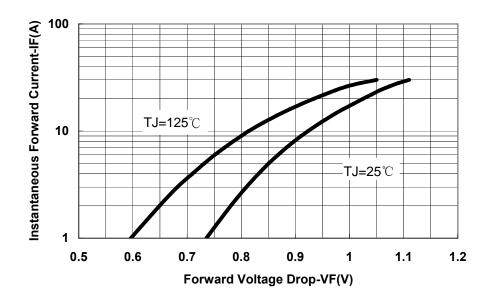


Fig.3-Typical Forward Voltage Drop Characteristics

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